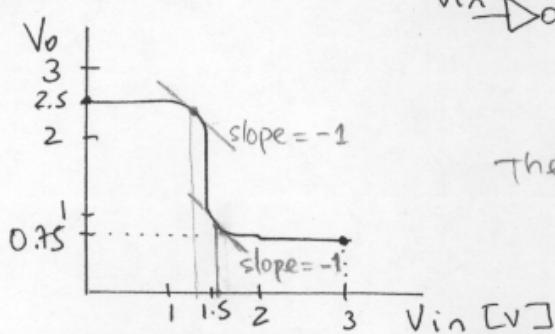


Your Name: Solution

Chapter 2: Problem 1 (10 points): Determine noise margins for the inverter with characteristics shown:



$V_{in} \rightarrow V_o$

$$V_{OL} = 0.75 \text{ V} ; V_{OH} = 2.5 \text{ V}$$

$$V_{iL} \approx 1.3 \text{ V} ; V_{iH} \approx 1.6 \text{ V}$$

Then,

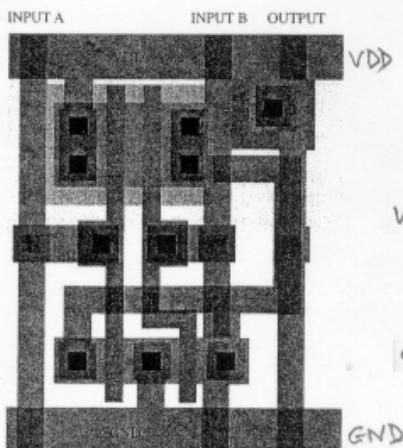
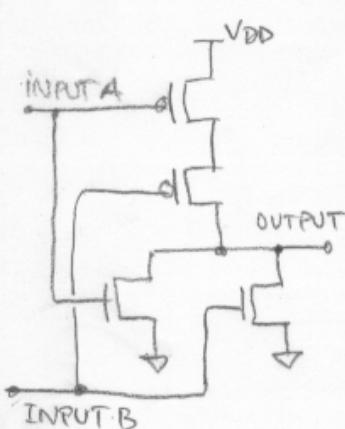
$$NM_H = V_{OH} - V_{iH} = 2.5 - 1.6 = 0.9 \text{ V}$$

$$NM_L = V_{iL} - V_{OL} = 1.3 - 0.75 = 0.55 \text{ V}$$

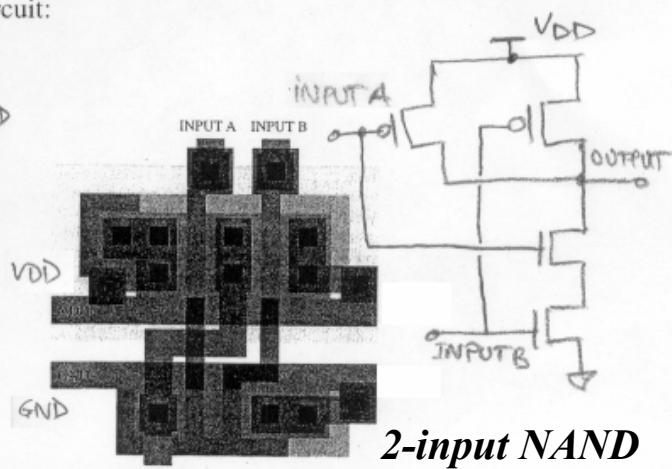
Chapter 2: Problem 2 (10 points): Fill in the name of the region that corresponds to the given transistor current expression:

$$I_{ds} = \begin{cases} 0 & \dots \text{region} = \text{cut-off} \\ \beta [(V_{gs} - V_t) V_{ds} - \frac{V_{ds}^2}{2}] & \dots \text{region} = \text{linear} \\ \frac{\beta}{2} (V_{gs} - V_t)^2 & \dots \text{region} = \text{saturation} \end{cases}$$

Chapter 2: Problem 2 (10 points): Do the reverse engineering on those two layouts (a) and (b). Draw the schematic diagram for each circuit:



2-input NOR



2-input NAND